PATENT ASSIGNMENT COVER SHEET

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EPAS ID: PAT8386469

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
HANG GU	12/28/2023
WEI GAO	12/28/2023
MAOZHOU DAI	12/28/2023

RECEIVING PARTY DATA

Name:	NOVUS SEMICONDUCTORS CO., LTD.
Street Address:	NO. 12-18, 9TH FLOOR, BUILDING 2, NO. 1366, MIDDLE SECTION OF TIANFU AVENUE, CHENGDU HIGH-TECH ZONE, SICHUAN
City:	CHENGDU
State/Country:	CHINA

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	18580161

CORRESPONDENCE DATA

Fax Number:

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

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ATTORNEY DOCKET NUMBER:	GBCDRD005
NAME OF SUBMITTER:	GOKALP BAYRAMOGLU
SIGNATURE:	/GOKALP BAYRAMOGLU/
DATE SIGNED:	01/18/2024

Total Attachments: 2

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Attorney Docket No. GBCDRD005

ASSIGNMENT

(1-8) Insert Name(s) of Inventor(s) (1) Hang GU (2) Wei GAO (3) Maozhou DAI

For good and valuable consideration receipt of which is hereby acknowledged, the undersigned agree(s) to assign, and hereby do(es) assign, transfer and set over to:

(9) Insert name of Assignee (9) NOVUS SEMICONDUCTORS CO., LTD.

(10) Insert state of incorporation of Assignee (10) China

(11) Insert address of Assignee (11) No. 12-18, 9th Floor, Building 2, No. 1366, Middle Section Of Tianfu Avenue, Chengdu High-tech Zone Chengdu, Sichuan, China

(hereinafter designated as the Assignee) the entire right, title, interest, and patent applications and patents within the United States, including divisions, reissues, continuations and all other extensions, rights and priorities in the invention known as and subject matter contained in

(12) Insert Identification of Invention, such as Title, Case Number or Foreign Application Number (12) TRENCH SiC MOSFET INTEGRATED WITH HIGH-SPEED FLYBACK DIODE AND PREPARATION METHOD THEREOF

(13) Insert Date of Filing of Application (13) Application is attached hereto.

1) The undersigned agree(s) to execute all papers necessary in connection with the application and any continuing or division applications thereof and also to execute separate assignments in connection with such applications as the Assignee may deem necessary or expedient.

2) The undersigned agree(s) to execute all papers necessary in connection with any interference which may be declared concerning this application or continuation or division thereof and to cooperate with the Assignee in every way possible in obtaining evidence and going forward with such interference.

3) The undersigned agree(s) to execute all papers and documents and perform any act which may be necessary in connection with claims or provisions of the International Convention for Protection of Industrial Property or similar agreements.

4) The undersigned agree(s) to perform all affirmative acts which may be necessary to obtain a grant of a valid United States patent to the Assignee.

5) The undersigned hereby authorize(s) and request(s) the Commissioner for Patents and the duly constituted authorities of foreign countries to issue any and all Letters Patents resulting from said application or any division or divisions or continuing or reissue applications thereof to the said Assignee, its successors and assigns, as Assignee of the entire right, title and interest, and hereby covenants that he has (they have) full right to convey the entire interest herein assigned, and that he has (they have) not executed and will not execute, any agreement in conflict herewith.

6) The undersigned hereby grant(s)

Gokalp Bayramoglu, Reg.No. 66305

the power to insert on this assignment any further identification which may be necessary or desirable in order to comply with the rules of the United States Patent and Trademark Office for recordation of this document.

Date Dec. 28. 2023

Hang Gu.

Hang GU

Date Dec. 28. 2023

Wei Gao

Wei GAO

Date Dec. 28. 2023

Maozhou Dai

Maozhou DAI